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Electronic Supplementary Information

Low-temperature wafer-scale synthesis of two-dimensional SnS₂

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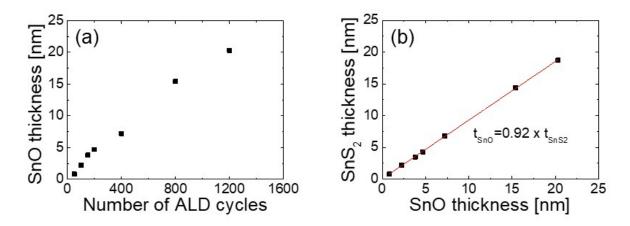


Fig. S1 (a) Variation in the SnO thickness as a function of number of ALD cycles and (b) Variation in the SnS_2 thickness as a function of the SnO thickness.

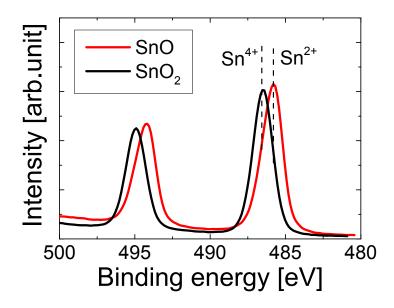


Fig. S2 XPS spectra of Sn 3d core level in the SnO and SnO_2 thin films grown by ALD.

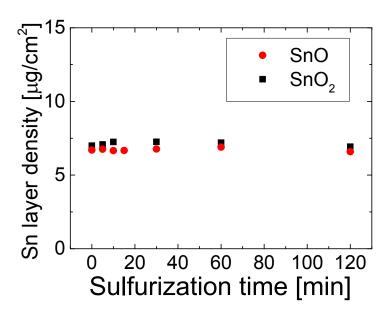


Fig. S3 Variation in the Sn layer density of the SnO and SnO_2 sulfurized at 350 °C as a function of the sulfurization time. The Sn layer density was measured using WDXRF.

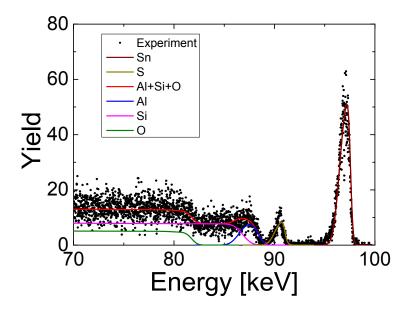


Fig. S4 MEIS spectrum for the 3 nm-thick SnO grown on $Al_2O_3/SiO_2/Si$ sulfurized at 350 °C for 60 min.

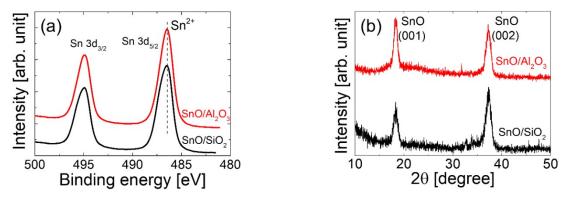
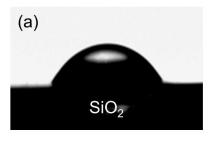


Fig. S5 (a) Sn 3d XPS spectra and (b) θ -2 θ XRD patterns of the ALD-grown SnO on amorphous Al₂O₃ and SiO₂.



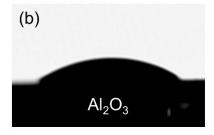


Fig. S6 Optical images of water droplet on (a) amorphous SiO_2 and (b) Al_2O_3 .